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September 2012

## FDMC86248

# N-Channel Power Trench<sup>®</sup> MOSFET 150 V, 13 A, 90 m $\Omega$

#### **Features**

- Max  $r_{DS(on)}$  = 90 m $\Omega$  at  $V_{GS}$  = 10 V,  $I_D$  = 3.4 A
- Max  $r_{DS(on)}$  = 125 m $\Omega$  at  $V_{GS}$  = 6 V,  $I_D$  = 2.9 A

Top

- Advanced Package and Silicon combination for low r<sub>DS(on)</sub> and high efficiency
- 100% UIL Tested
- RoHS Compliant

#### **General Description**

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced Power Trench® process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

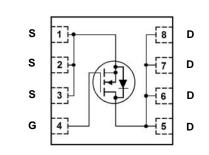
#### **Applications**

- Primary MOSFET
- MV synchronous rectifier



**Bottom** 





Power 33

### MOSFET Maximum Ratings T<sub>A</sub> = 25 °C unless otherwise noted

Symbol	Parameter			Ratings	Units
V <sub>DS</sub>	Drain to Source Voltage			150	V
$V_{GS}$	Gate to Source Voltage			±20	V
	Drain Current -Continuous	T <sub>C</sub> = 25 °C		13	
I <sub>D</sub>	-Continuous	T <sub>A</sub> = 25 °C	(Note 1a)	3.4	Α
	-Pulsed			15	
E <sub>AS</sub>	Single Pulse Avalanche Energy		(Note 3)	37	mJ
Б	Power Dissipation	T <sub>C</sub> = 25 °C		36	W
$P_{D}$	Power Dissipation	T <sub>A</sub> = 25 °C	(Note 1a)	2.3	VV
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Tempera	ature Range		-55 to +150	°C

#### **Thermal Characteristics**

$R_{\theta JC}$	Thermal Resistance, Junction to Case	3.4	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	53	C/VV

#### **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC86248	FDMC86248	Power 33	13 "	12 mm	3000 units

### **Electrical Characteristics** T<sub>J</sub> = 25 °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	cteristics					
$BV_DSS$	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	150			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, referenced to 25 °C		104		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 120 V, V <sub>GS</sub> = 0 V			1	μΑ
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA

#### On Characteristics

V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$	2.0	3.2	4.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250 \mu A$ , referenced to 25 °C		-9		mV/°C
		$V_{GS} = 10 \text{ V}, I_D = 3.4 \text{ A}$		69	90	
r <sub>DS(on)</sub>	Static Drain to Source On Resistance	$V_{GS} = 6 \text{ V}, I_D = 2.9 \text{ A}$		89	125	mΩ
	$V_{GS} = 10 \text{ V}, I_D = 3.4 \text{ A}, T_J = 125 ^{\circ}\text{C}$		140	183		
g <sub>FS</sub>	Forward Transconductance	$V_{DS} = 10 \text{ V}, I_{D} = 3.4 \text{ A}$		10		S

#### **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V 75.V.V 0.V	393	525	pF
Coss	Output Capacitance	$V_{DS} = 75 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1  MHz	50	70	рF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 1 1/1/12	2.6	5.0	pF
R <sub>a</sub>	Gate Resistance		0.8	2.0	Ω

#### **Switching Characteristics**

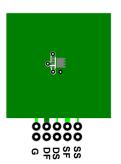
t <sub>d(on)</sub>	Turn-On Delay Time			6.9	14	ns
t <sub>r</sub>	Rise Time	$V_{DD} = 75 \text{ V}, I_{D} = 3.4 \text{ A},$		1.4	10	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS} = 10 \text{ V}, R_{GEN} = 6 \Omega$		11	20	ns
t <sub>f</sub>	Fall Time			2.8	10	ns
$Q_{g(TOT)}$	Total Gate Charge	V <sub>GS</sub> = 0 V to 10 V		6.4	9.0	nC
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 0 \text{ V to 5 V}$ $V_{DD} = 75$	) V,	3.7	5.2	nC
$Q_{gs}$	Gate to Source Charge	I <sub>D</sub> = 3.4 F	`	1.9		nC
$Q_{gd}$	Gate to Drain "Miller" Charge			1.7		nC

#### **Drain-Source Diode Characteristics**

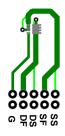
V	Source to Drain Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 3.4 A (Note 2)		0.80	1.3	V	
v SD	V <sub>SD</sub> Source to Drain Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = 2 \text{ A}$	(Note 2)		0.78	1.2	v
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> = 3.4 A, di/dt = 100 A/μs		54	86	ns	
Q <sub>rr</sub>	Reverse Recovery Charge				48	77	nC

#### NOTES:

<sup>1.</sup> R<sub>0JA</sub> is determined with the device mounted on a 1 in<sup>2</sup> pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. R<sub>0JC</sub> is guaranteed by design while R<sub>0CA</sub> is determined by the user's board design.



a. 53 °C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper



b. 125 °C/W when mounted on a minimum pad of 2 oz copper

<sup>2.</sup> Pulse Test: Pulse Width < 300  $\mu s,$  Duty cycle < 2.0%.

<sup>3.</sup> E<sub>AS</sub> of 37 mJ is based on starting T<sub>J</sub> = 25 °C; N-ch: L = 3 mH, I<sub>AS</sub> = 5 A, V<sub>DD</sub> = 150 V, V<sub>GS</sub> = 10 V. 100% test at L = 0.3 mH, I<sub>AS</sub> = 12 A.

#### Typical Characteristics T<sub>J</sub> = 25 °C unless otherwise noted

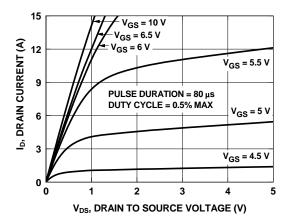


Figure 1. On-Region Characteristics

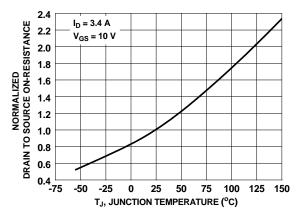


Figure 3. Normalized On-Resistance vs Junction Temperature

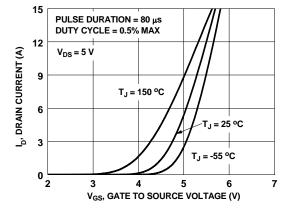


Figure 5. Transfer Characteristics

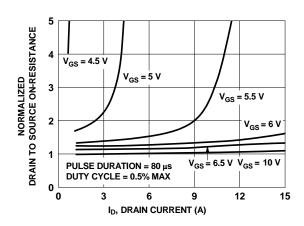


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

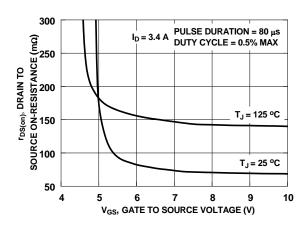


Figure 4. On-Resistance vs Gate to Source Voltage

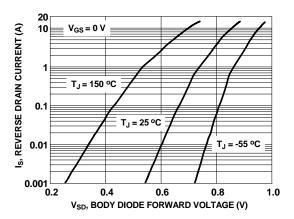


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

### **Typical Characteristics** $T_J = 25$ °C unless otherwise noted

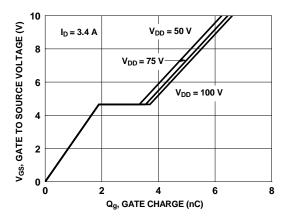


Figure 7. Gate Charge Characteristics

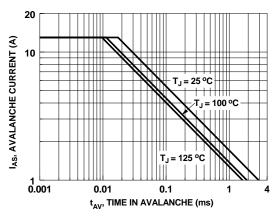


Figure 9. Unclamped Inductive Switching Capability

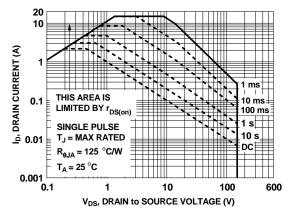


Figure 11. Forward Bias Safe Operating Area

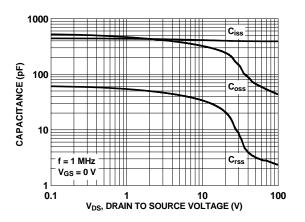


Figure 8. Capacitance vs Drain to Source Voltage

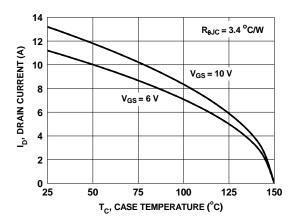


Figure 10. Maximum Continuous Drain Current vs Case Temperature

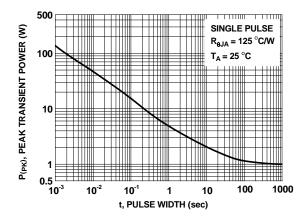


Figure 12. Single Pulse Maximum Power Dissipation

## Typical Characteristics T<sub>J</sub> = 25 °C unless otherwise noted

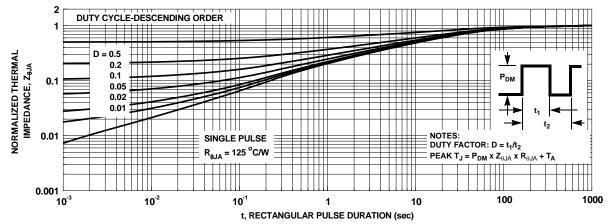
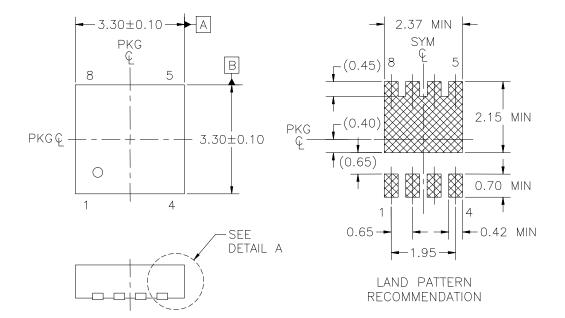
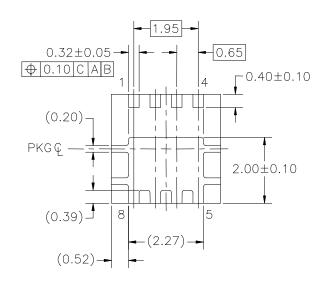
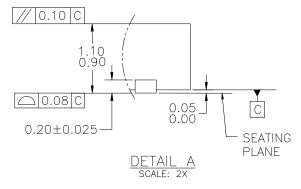


Figure 13. Junction-to-Ambient Transient Thermal Response Curve

### **Dimensional Outline and Pad Layout**







PQFN08BREV1

NOTES: UNLESS OTHERWISE SPECIFIED

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- B) ALL DIMENSIONS ARE IN MILLIMETERS.
  C) DIMENSIONS DO NOT INCLUDE BURRS
- OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
- D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
- E) DRAWING FILE NAME: PQFN08BREV1





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